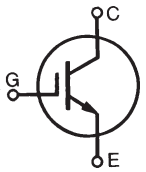
IXYS

Advance Technical Information

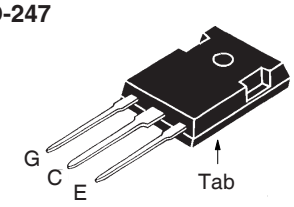
# High Voltage XPT™ IGBT

# IXYH24N170C

$V_{CES}$ = 1700V
$I_{C110}$ = 24A
$V_{CE(sat)}$ ≤ 3.8V
$t_{fi(typ)}$ = 50ns




**TO-247**




G = Gate C = Collector
E = Emitter Tab = Collector

| Symbol | Test Conditions | Maximum Ratings | |
|---|---|---|---|
| $V_{CES}$ | $T_J$ = 25°C to 175°C | 1700 | V |
| $V_{CGR}$ | $T_J$ = 25°C to 175°C, $R_{GE}$ = 1MΩ | 1700 | V |
| $V_{GES}$ | Continuous | ±20 | V |
| $V_{GEM}$ | Transient | ±30 | V |
| $I_{C25}$ | $T_C$ = 25°C | 58 | A |
| $I_{C110}$ | $T_C$ = 110°C | 24 | A |
| $I_{CM}$ | $T_C$ = 25°C, 1ms | 145 | A |
| **SSOA** | $V_{GE}$ = 15V, $T_{VJ}$ = 150°C, $R_G$ = 5Ω | $I_{CM}$ = 48 | A |
| **(RBSOA)** | Clamped Inductive Load | $V_{CE}$ ≤ 1360 | V |
| $P_C$ | $T_C$ = 25°C | 500 | W |
| $T_J$ | | -55 ... +175 | °C |
| $T_{JM}$ | | 175 | °C |
| $T_{stg}$ | | -55 ... +175 | °C |
| $T_L$ | Maximum Lead Temperature for Soldering | 300 | °C |
| $T_{SOLD}$ | 1.6 mm (0.062in.) from Case for 10s | 260 | °C |
| $M_d$ | Mounting Torque | 1.13/10 | Nm/lb.in |
| **Weight** | | 6 | g |

### Features

- High Voltage Package
- High Blocking Voltage
- High Peak Current Capability
- Low Saturation Voltage

### Advantages

- Low Gate Drive Requirement
- High Power Density

### Applications

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- Laser Generators
- Capacitor Discharge Circuits
- AC Switches

| Symbol | Test Conditions ($T_J$ = 25°C, Unless Otherwise Specified) | Characteristic Values Min. | Typ. | Max. | |
|---|---|---|---|---|---|
| $BV_{CES}$ | $I_C$ = 250μA, $V_{GE}$ = 0V | 1700 | | | V |
| $V_{GE(th)}$ | $I_C$ = 250μA, $V_{CE}$ = $V_{GE}$ | 3.0 | | 5.0 | V |
| $I_{CES}$ | $V_{CE}$ = $V_{CES}$, $V_{GE}$ = 0V | | | 25 | μA |
| | $T_J$ = 150°C | | | 3.5 | mA |
| $I_{GES}$ | $V_{CE}$ = 0V, $V_{GE}$ = ±20V | | | ±100 | nA |
| $V_{CE(sat)}$ | $I_C$ = 20A, $V_{GE}$ = 15V, Note 1 | | 3.2 | 3.8 | V |
| | $T_J$ = 150°C | | 5.0 | | V |

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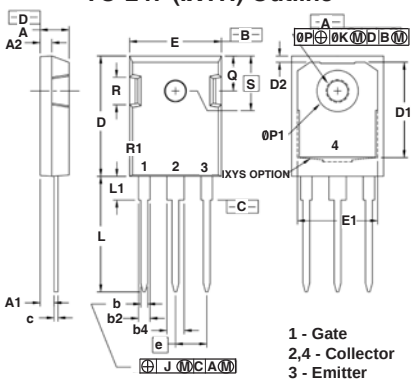
| Symbol | Test Conditions ($T_J$ = 25°C Unless Otherwise Specified) | Characteristic Values Min. | Typ. | Max. |
|---|---|---|---|---|
| $g_{fs}$ | $I_C$ = 24A, $V_{CE}$ = 10V, Note 1 | 12 | 20 | S |
| $C_{ies}$ | $V_{CE}$ = 25V, $V_{GE}$ = 0V, f = 1MHz | | 2000 | pF |
| $C_{oes}$ | | | 106 | pF |
| $C_{res}$ | | | 40 | pF |
| $Q_{g(on)}$ | $I_C$ = 24A, $V_{GE}$ = 15V, $V_{CE}$ = 0.5 • $V_{CES}$ | | 96 | nC |
| $Q_{ge}$ | | | 11 | nC |
| $Q_{gc}$ | | | 44 | nC |
| $t_{d(on)}$ | **Inductive load, $T_J$ = 25°C** | | 12 | ns |
| $t_{ri}$ | $I_C$ = 24A, $V_{GE}$ = 15V | | 30 | ns |
| $E_{on}$ | $V_{CE}$ = 850V, $R_G$ = 5Ω | | 4.90 | mJ |
| $t_{d(off)}$ | Note 2 | | 160 | ns |
| $t_{fi}$ | | | 50 | ns |
| $E_{off}$ | | | 1.95 | mJ |
| $t_{d(on)}$ | **Inductive load, $T_J$ = 150°C** | | 11 | ns |
| $t_{ri}$ | $I_C$ = 24A, $V_{GE}$ = 15V | | 33 | ns |
| $E_{on}$ | $V_{CE}$ = 850V, $R_G$ = 5Ω | | 6.30 | mJ |
| $t_{d(off)}$ | Note 2 | | 150 | ns |
| $t_{fi}$ | | | 120 | ns |
| $E_{off}$ | | | 2.70 | mJ |
| $R_{thJC}$ | | | | 0.30 °C/W |
| $R_{thCS}$ | | | 0.21 | °C/W |

**TO-247 (IXYH) Outline**




1 - Gate
2,4 - Collector
3 - Emitter

| Dim. | Millimeter min | Millimeter max | Inches min | Inches max |
|---|---|---|---|---|
| A | 4.70 | 5.30 | 0.185 | 0.209 |
| A1 | 2.21 | 2.59 | 0.087 | 0.102 |
| A2 | 1.50 | 2.49 | 0.059 | 0.098 |
| b | 0.99 | 1.40 | 0.039 | 0.055 |
| b2 | 1.65 | 2.39 | 0.065 | 0.094 |
| b4 | 2.59 | 3.43 | 0.102 | 0.135 |
| c | 0.38 | 0.89 | 0.015 | 0.035 |
| D | 20.79 | 21.45 | 0.819 | 0.845 |
| D1 | 13.07 | - | 0.515 | - |
| D2 | 0.51 | 1.35 | 0.020 | 0.053 |
| E | 15.48 | 16.24 | 0.610 | 0.640 |
| E1 | 13.45 | - | 0.53 | - |
| E2 | 4.31 | 5.48 | 0.170 | 0.216 |
| e | 5.45 BSC | | 0.215 BSC | |
| L | 19.80 | 20.30 | 0.078 | 0.800 |
| L1 | - | 4.49 | - | 0.177 |
| Ø P | 3.55 | 3.65 | 0.140 | 0.144 |
| Ø P1 | - | 7.39 | - | 0.290 |
| Q | 5.38 | 6.19 | 0.212 | 0.244 |
| S | 6.14 BSC | | 0.242 BSC | |

Notes:

1. Pulse test, t ≤ 300µs, duty cycle, d ≤ 2%.
2. Switching times & energy losses may increase for higher $V_{CE}$(clamp), $T_J$ or $R_G$.

**ADVANCE TECHNICAL INFORMATION**

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,860,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

**Fig. 1. Output Characteristics @ $T_J$ = 25ºC**

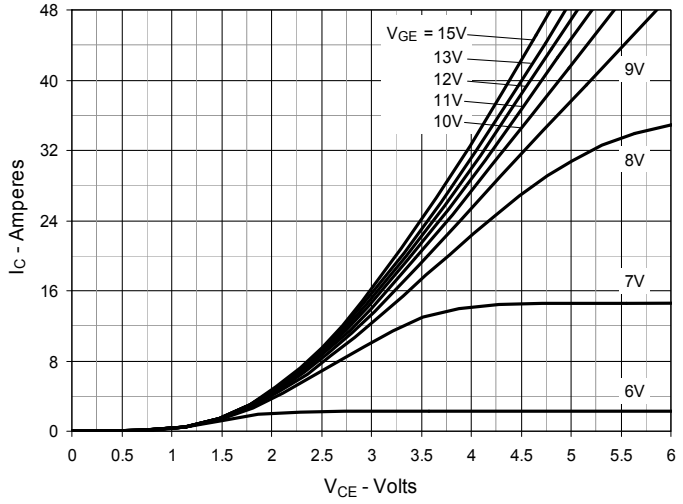



**Fig. 2. Extended Output Characteristics @ $T_J$ = 25ºC**

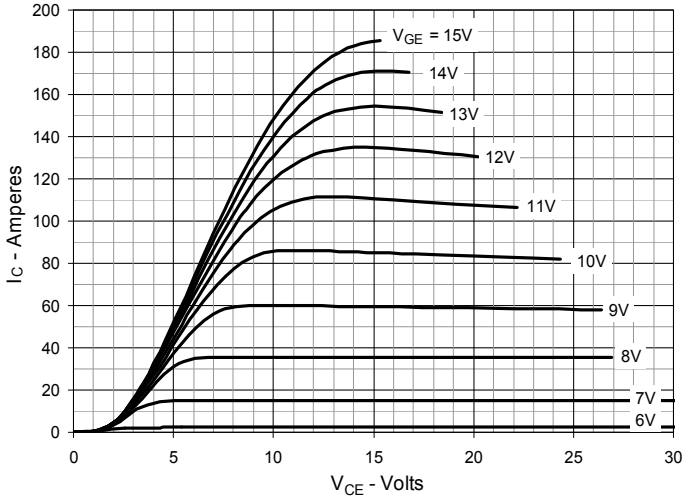



**Fig. 3. Output Characteristics @ $T_J$ = 150ºC**

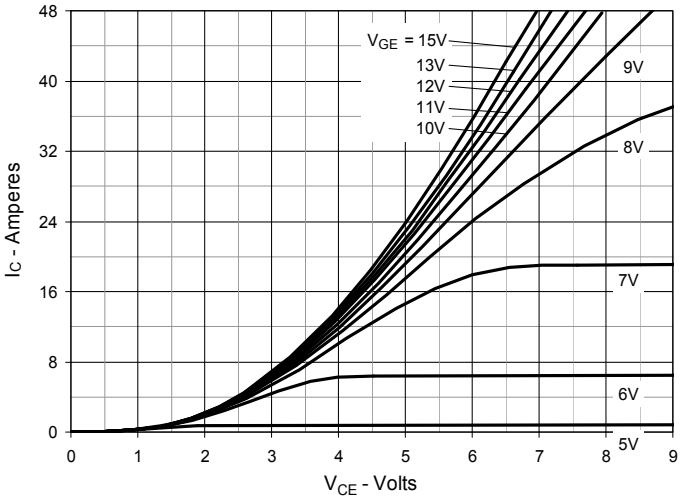



**Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature**

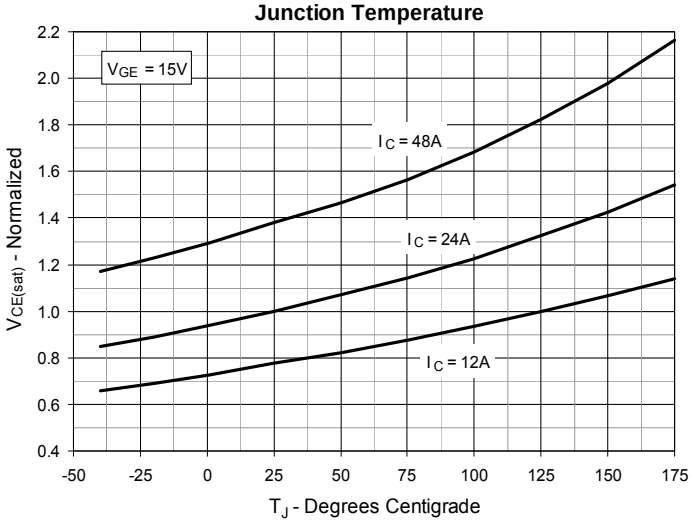



**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**

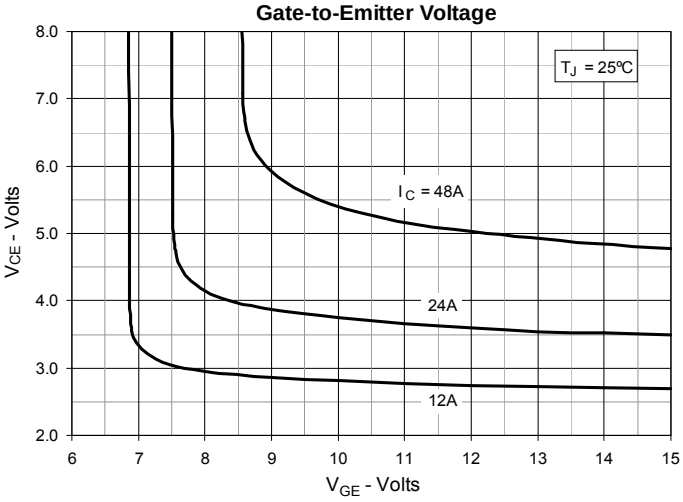



**Fig. 6. Input Admittance**

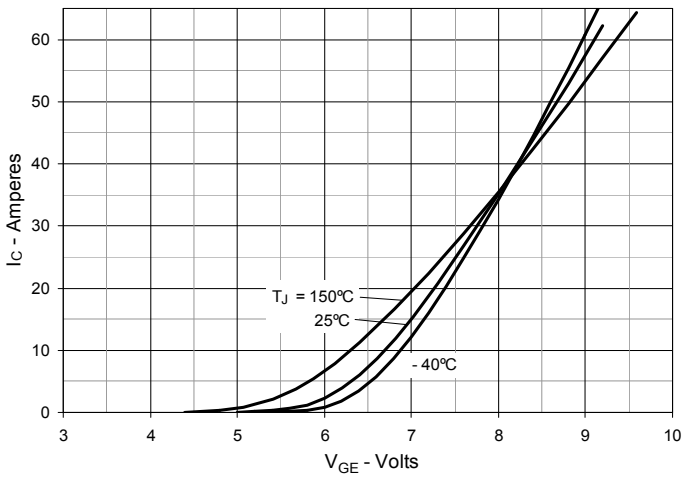



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**Fig. 7. Transconductance**

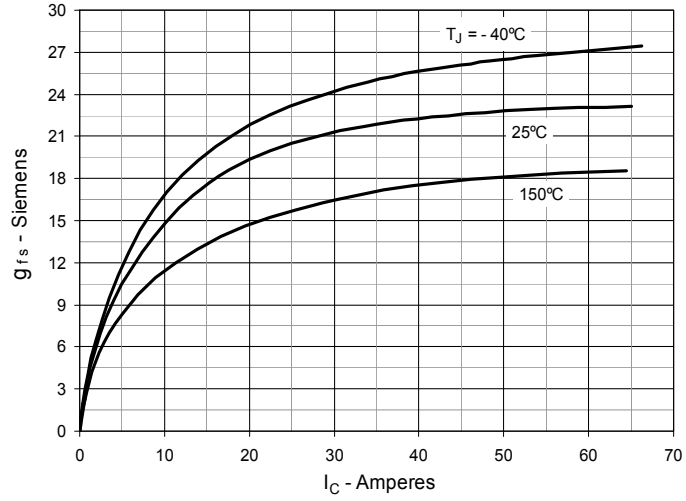



**Fig. 8. Gate Charge**

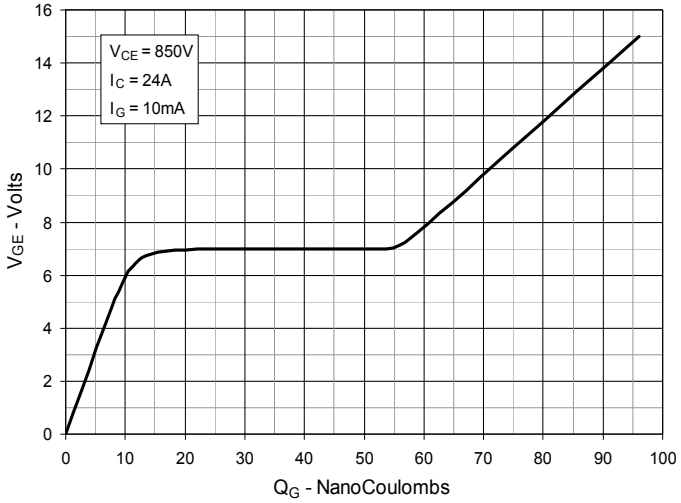



**Fig. 9. Capacitance**

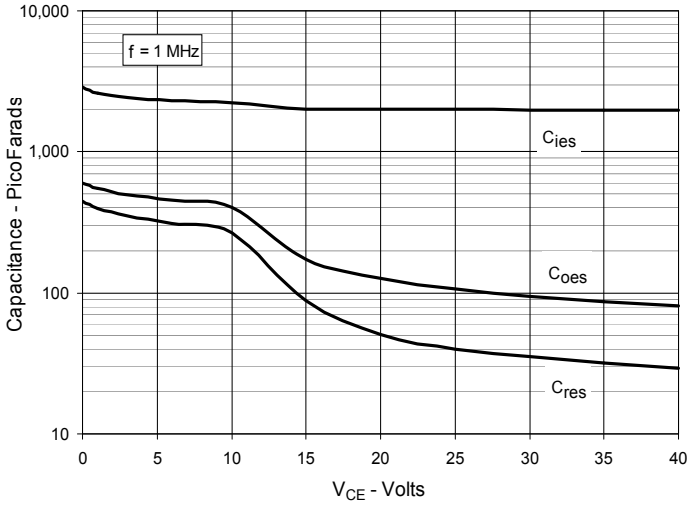



**Fig. 10. Reverse-Bias Safe Operating Area**

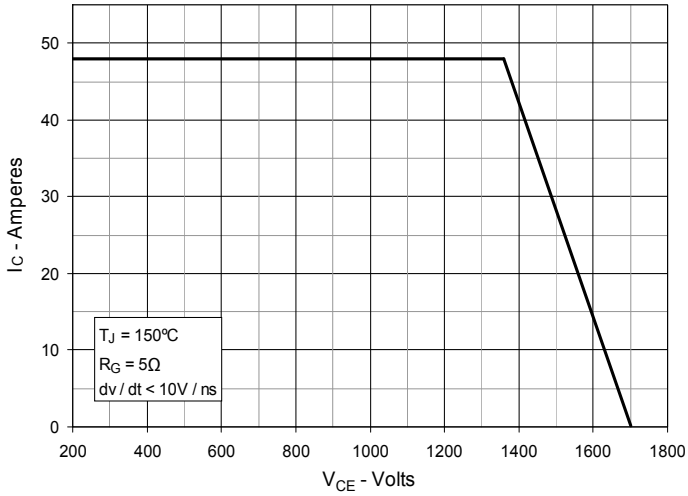
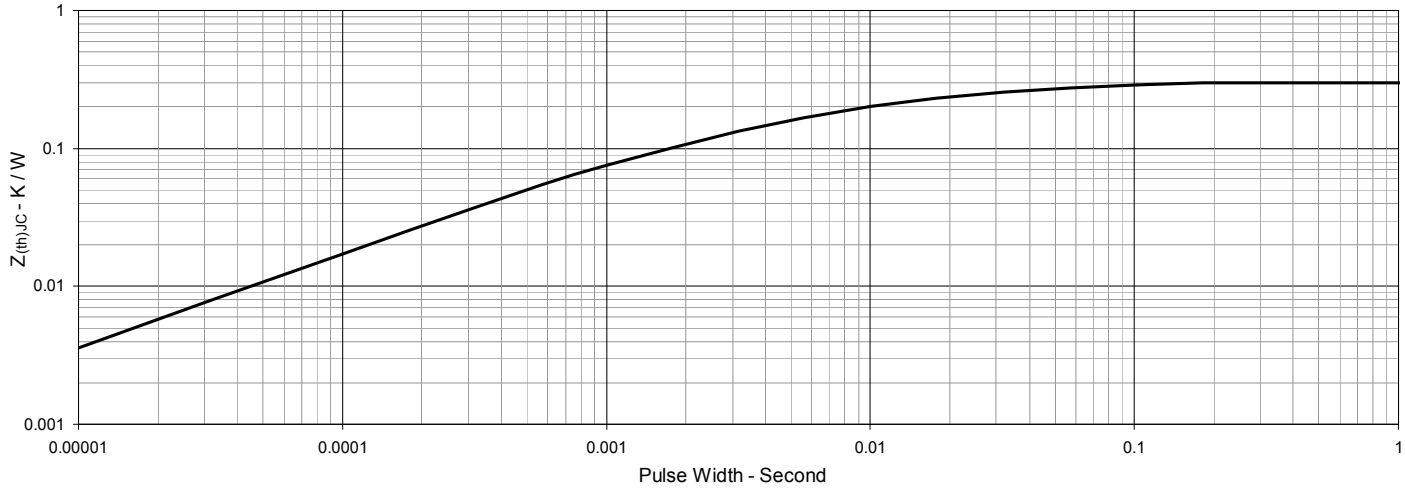



**Fig. 11. Maximum Transient Thermal Impedance**




IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**

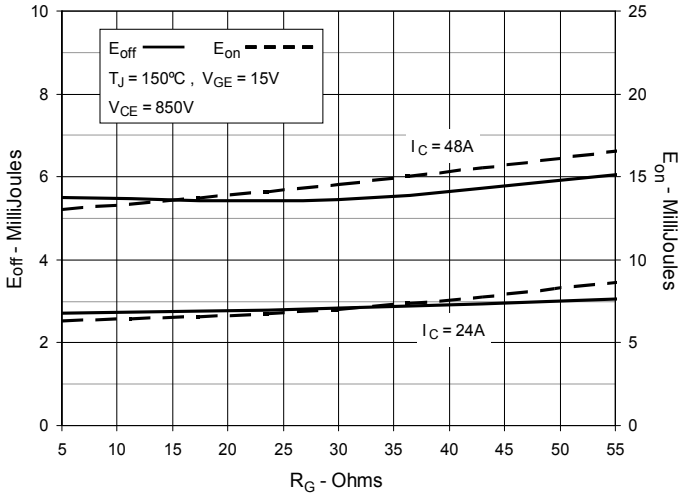



**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**

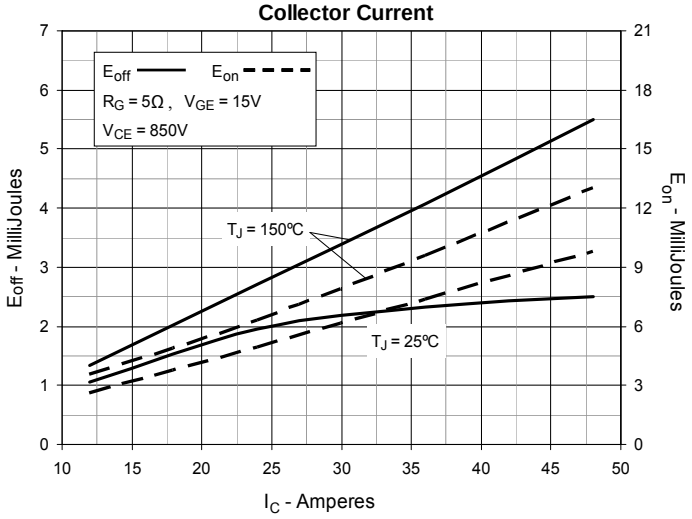



**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**

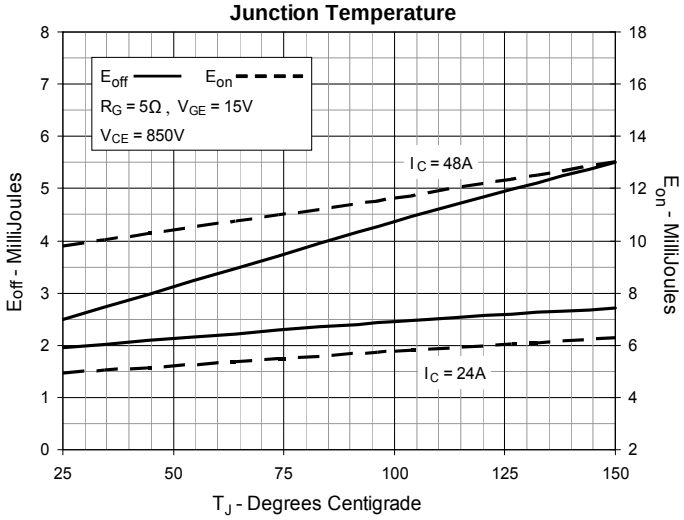



**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**

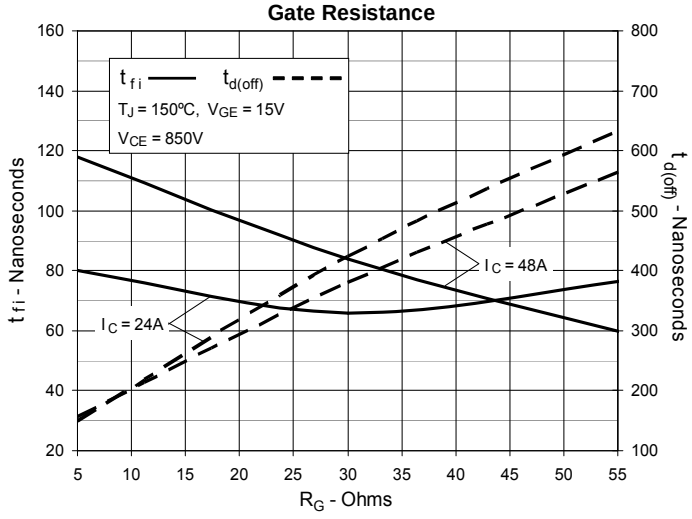



**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**

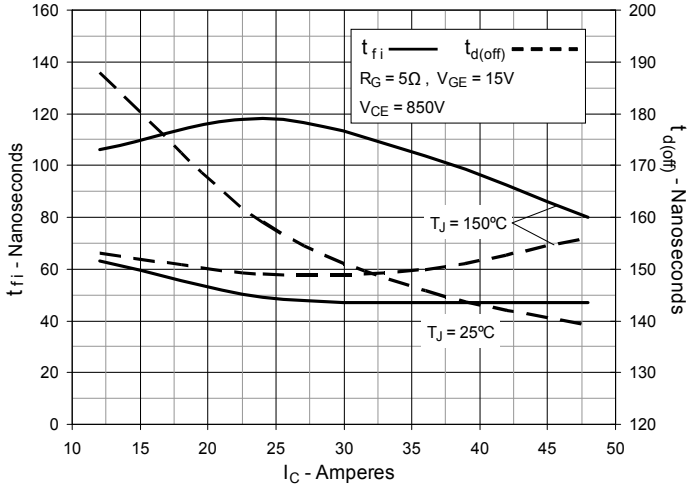



**Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature**

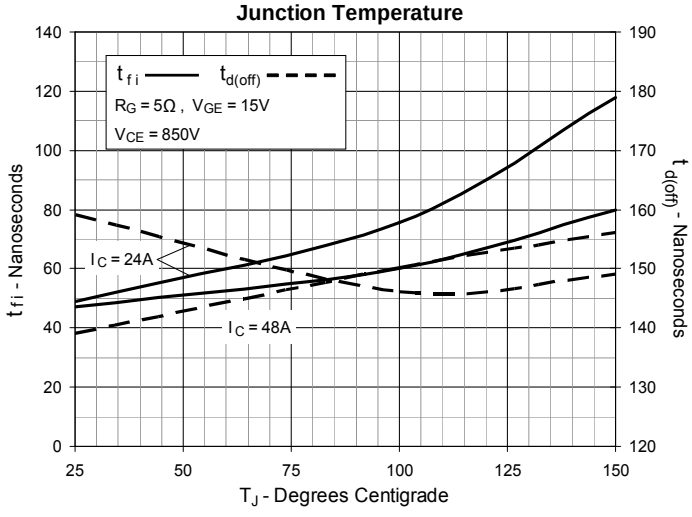



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**Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance**

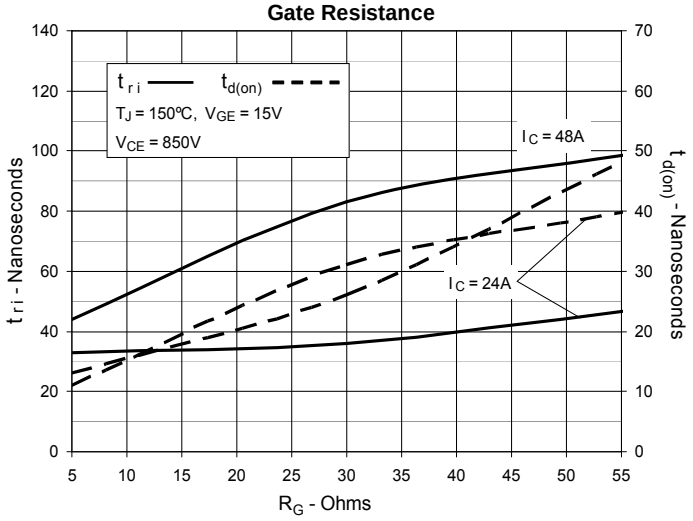
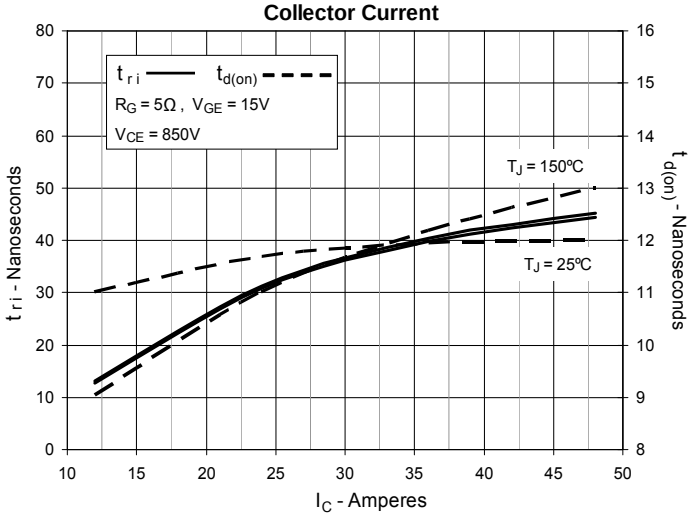



**Fig. 19. Inductive Turn-on Switching Times vs. Collector Current**



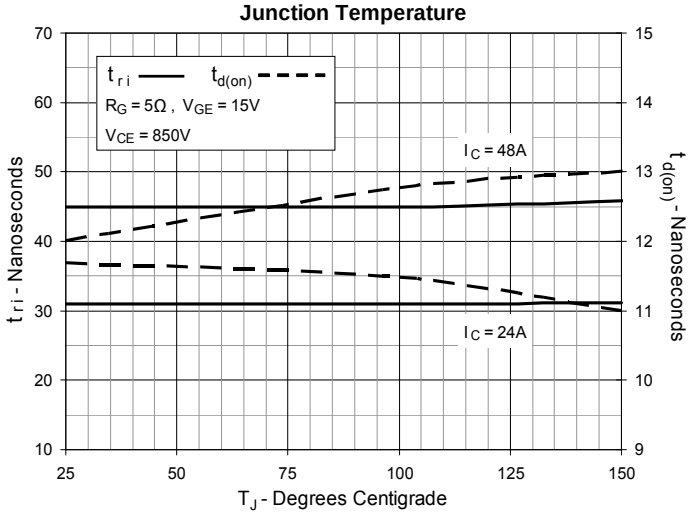


**Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature**